

<b>Interview Summary</b>	Application No. 10/749,599	Applicant(s) EJIRI, KAZUAKI	
	Examiner Lee, Calvin	Art Unit 2818	

All participants (applicant, applicant's representative, PTO personnel):

- (1) Calvin Lee. (3)\_\_\_\_\_.
- (2) Donald W. Muirhead. (4)\_\_\_\_\_.

Date of Interview: 06 September 2005.

Type: a) ☒ Telephonic b) ☐ Video Conference  
c) ☐ Personal [copy given to: 1) ☐ applicant 2) ☐ applicant's representative]

Exhibit shown or demonstration conducted: d) ☐ Yes e) ☒ No.  
If Yes, brief description: \_\_\_\_\_.

Claim(s) discussed: 1-3 and 10.

Identification of prior art discussed: N/A.

Agreement with respect to the claims f) ☒ was reached. g) ☐ was not reached. h) ☐ N/A.

Substance of Interview including description of the general nature of what was agreed to if an agreement was reached, or any other comments: See Continuation Sheet.

(A fuller description, if necessary, and a copy of the amendments which the examiner agreed would render the claims allowable, if available, must be attached. Also, where no copy of the amendments that would render the claims allowable is available, a summary thereof must be attached.)

THE FORMAL WRITTEN REPLY TO THE LAST OFFICE ACTION MUST INCLUDE THE SUBSTANCE OF THE INTERVIEW. (See MPEP Section 713.04). If a reply to the last Office action has already been filed, APPLICANT IS GIVEN ONE MONTH FROM THIS INTERVIEW DATE, OR THE MAILING DATE OF THIS INTERVIEW SUMMARY FORM, WHICHEVER IS LATER, TO FILE A STATEMENT OF THE SUBSTANCE OF THE INTERVIEW. See Summary of Record of Interview requirements on reverse side or on attached sheet.

Examiner Note: You must sign this form unless it is an Attachment to a signed Office action.

\_\_\_\_\_  
Examiner's signature, if required

Continuation of Substance of Interview including description of the general nature of what was agreed to if an agreement was reached, or any other comments:

Claim 1, line 6, after "abrasive slurry" inserted --, wherein said low-k material insulating layer is formed as a SiCOH layer or as a methyl silsesquioxane layer--;

Claim 1, line 9, after "polishing pad" insert --washing said semiconductor wafer, which is drenched with said aqueous abrasive slurry, with an aqueous washing solution; and rinsing the washed semiconductor wafer--;

Canceled claims 2-3;

Claim 10, line 2, after "further comprising" deleted --washing said semiconductor wafer, which is drenched with said aqueous abrasive slurry, with an aqueous washing solution; and--